

# ISL9R860PF2

## 8 A, 600 V, STEALTH™ Diode

### Description

The ISL9R860PF2 is a STEALTH diode optimized for low loss performance in high frequency hard switched applications. The STEALTH family exhibits low reverse recovery current ( $I_{rr}$ ) and exceptionally soft recovery under typical operating conditions. This device is intended for use as a free wheeling or boost diode in power supplies and other power switching applications. The low  $I_{rr}$  and short  $t_a$  phase reduce loss in switching transistors. The soft recovery minimizes ringing, expanding the range of conditions under which the diode may be operated without the use of additional snubber circuitry. Consider using the STEALTH diode with an SMPS IGBT to provide the most efficient and highest power density design at lower cost.

### Features

- Stealth Recovery  $t_{rr} = 28$  ns (@  $I_F = 8$  A)
- Max Forward Voltage,  $V_F = 2.4$  V (@  $T_C = 25^\circ\text{C}$ )
- 600 V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- This Device is Pb-Free and is RoHS Compliant

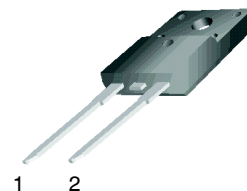
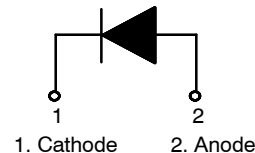
### Applications

- Switch Mode Power Supplies
- Hard Switched PFC Boost Diode
- UPS Free Wheeling Diode
- Motor Drive FWD
- SMPS FWD
- Snubber Diode



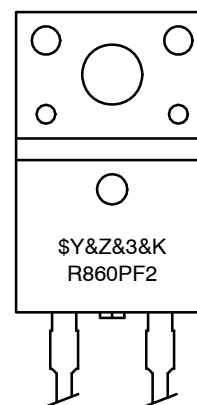
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TO-220, 2-Lead  
CASE 221AS

### MARKING DIAGRAM



|         |                           |
|---------|---------------------------|
| \$Y     | = ON Semiconductor Logo   |
| &Z&3    | = Data Code (Year & Week) |
| &K      | = Lot                     |
| R860PF2 | = Specific Device Code    |

### ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

# ISL9R860PF2

## MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol         | Parameter                                                                          | Rating     | Units            |
|----------------|------------------------------------------------------------------------------------|------------|------------------|
| $V_{RRM}$      | Peak Repetitive Reverse Voltage                                                    | 600        | V                |
| $V_{RWM}$      | Working Peak Reverse Voltage                                                       | 600        | V                |
| $V_R$          | DC Blocking Voltage                                                                | 600        | V                |
| $I_{F(AV)}$    | Average Rectified Forward Current ( $T_C = 75^\circ\text{C}$ )                     | 8          | A                |
| $I_{FRM}$      | Repetitive Peak Surge Current (20 kHz Square Wave)                                 | 16         | A                |
| $I_{FSM}$      | Nonrepetitive Peak Surge Current (Halfwave 1 Phase 60 Hz)                          | 100        | A                |
| $P_D$          | Power Dissipation                                                                  | 26         | W                |
| $E_{AVL}$      | Avalanche Energy (1 A, 40 mH)                                                      | 20         | mJ               |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range                                            | -55 to 175 | $^\circ\text{C}$ |
| $T_L$          | Maximum Temperature for Soldering<br>Leads at 0.063 in (1.6 mm) from Case for 10 s | 300        | $^\circ\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## ELECTRICAL CHARACTERISTICS $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Condition | Min | Typ | Max | Unit |
|--------|-----------|----------------|-----|-----|-----|------|
|--------|-----------|----------------|-----|-----|-----|------|

### OFF STATE CHARACTERISTICS

|       |                               |                      |                           |   |   |     |               |
|-------|-------------------------------|----------------------|---------------------------|---|---|-----|---------------|
| $I_R$ | Instantaneous Reverse Current | $V_R = 600\text{ V}$ | $T_C = 25^\circ\text{C}$  | – | – | 100 | $\mu\text{A}$ |
|       |                               |                      | $T_C = 125^\circ\text{C}$ | – | – | 1.0 | mA            |

### ON STATE CHARACTERISTICS

|       |                               |                    |                           |   |     |     |   |
|-------|-------------------------------|--------------------|---------------------------|---|-----|-----|---|
| $V_F$ | Instantaneous Forward Voltage | $I_F = 8\text{ A}$ | $T_C = 25^\circ\text{C}$  | – | 2.0 | 2.4 | V |
|       |                               |                    | $T_C = 125^\circ\text{C}$ | – | 1.6 | 2.0 | V |

### DYNAMIC CHARACTERISTICS

|       |                      |                                       |   |    |   |    |
|-------|----------------------|---------------------------------------|---|----|---|----|
| $C_J$ | Junction Capacitance | $V_R = 10\text{ V}, I_F = 0\text{ A}$ | – | 30 | – | pF |
|-------|----------------------|---------------------------------------|---|----|---|----|

### SWITCHING CHARACTERISTICS

|           |                                  |                                                                                                     |   |     |    |                  |
|-----------|----------------------------------|-----------------------------------------------------------------------------------------------------|---|-----|----|------------------|
| $t_{rr}$  | Reverse Recovery Time            | $I_F = 1\text{ A}, di_F/dt = 100\text{ A}/\mu\text{s}, V_R = 30\text{ V}$                           | – | 18  | 25 | ns               |
|           |                                  | $I_F = 8\text{ A}, di_F/dt = 100\text{ A}/\mu\text{s}, V_R = 30\text{ V}$                           | – | 21  | 30 | ns               |
| $t_{rr}$  | Reverse Recovery Time            | $I_F = 8\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}, V_R = 390\text{ V}, T_C = 25^\circ\text{C}$  | – | 28  | –  | ns               |
| $I_{rr}$  | Maximum Reverse Recovery Current |                                                                                                     | – | 3.2 | –  | A                |
| $Q_{rr}$  | Reverse Recovery Charge          |                                                                                                     | – | 50  | –  | nC               |
| $t_{rr}$  | Reverse Recovery Time            | $I_F = 8\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}, V_R = 390\text{ V}, T_C = 125^\circ\text{C}$ | – | 77  | –  | ns               |
| $S$       | Softness Factor ( $t_b/t_a$ )    |                                                                                                     | – | 3.7 | –  |                  |
| $I_{rr}$  | Maximum Reverse Recovery Current |                                                                                                     | – | 3.4 | –  | A                |
| $Q_{rr}$  | Reverse Recovery Charge          |                                                                                                     | – | 150 | –  | nC               |
| $t_{rr}$  | Reverse Recovery Time            | $I_F = 8\text{ A}, di_F/dt = 600\text{ A}/\mu\text{s}, V_R = 390\text{ V}, T_C = 125^\circ\text{C}$ | – | 53  | –  | ns               |
| $S$       | Softness Factor ( $t_b/t_a$ )    |                                                                                                     | – | 2.5 | –  |                  |
| $I_{rr}$  | Maximum Reverse Recovery Current |                                                                                                     | – | 6.5 | –  | A                |
| $Q_{rr}$  | Reverse Recovery Charge          |                                                                                                     | – | 195 | –  | nC               |
| $di_M/dt$ | Maximum $di/dt$ during $t_b$     |                                                                                                     | – | 500 | –  | A/ $\mu\text{s}$ |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# ISL9R860PF2

## THERMAL CHARACTERISTICS $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol          | Parameter                               | Test Condition | Min | Typ | Max | Unit                      |
|-----------------|-----------------------------------------|----------------|-----|-----|-----|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case    |                | –   | –   | 4.8 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | TO-220F        | –   | –   | 70  | $^\circ\text{C}/\text{W}$ |

## PACKAGE MARKING AND ORDERING INFORMATION

| Part Number | Top Mark | Package    | Packing Method | Reel Size | Tape Width | Quantity |
|-------------|----------|------------|----------------|-----------|------------|----------|
| ISL9R860PF2 | R860PF2  | TO-220F-2L | Tube           | N/A       | N/A        | 50       |

## TYPICAL CHARACTERISTICS

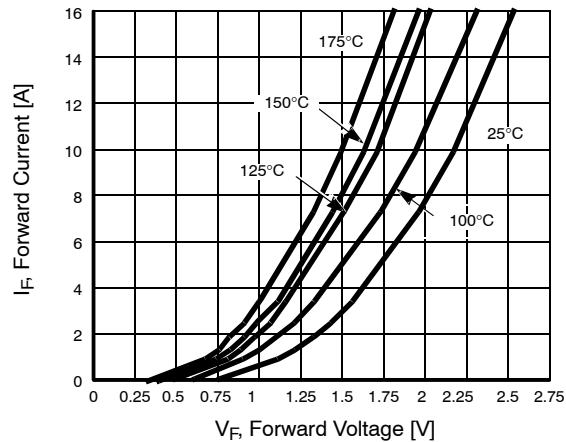


Figure 1. Forward Current vs. Forward Voltage

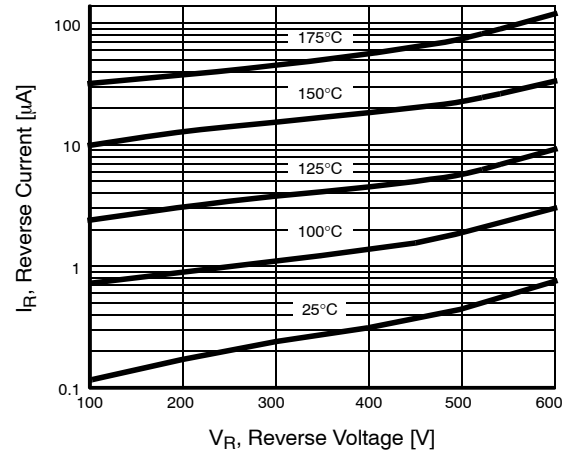


Figure 2. Reverse Current vs. Reverse Voltage

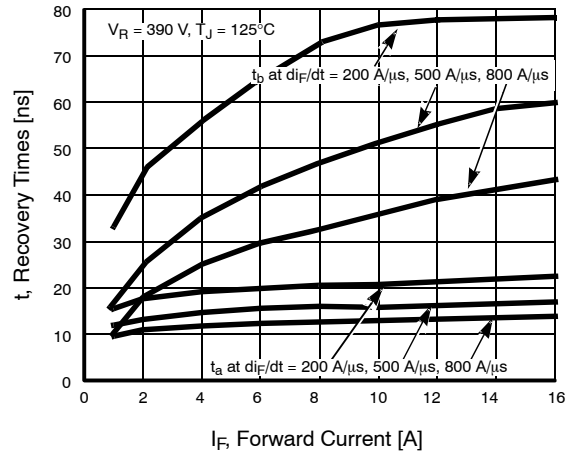


Figure 3.  $t_a$  and  $t_b$  Curves vs. Forward Current

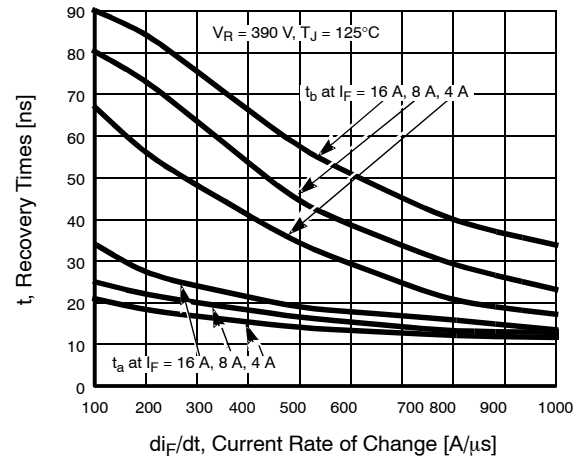


Figure 4.  $t_a$  and  $t_b$  Curves vs.  $di_F/dt$

TYPICAL CHARACTERISTICS (continued)

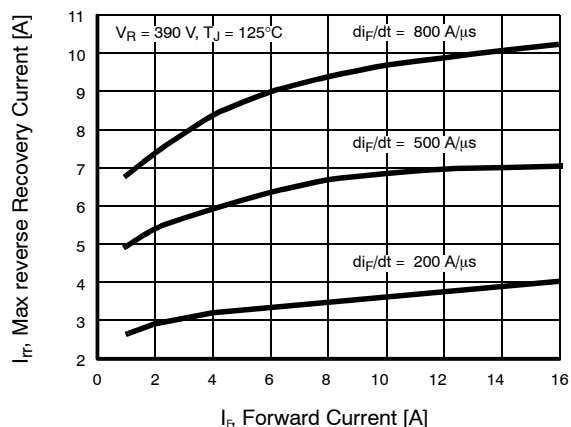


Figure 5. Maximum Reverse Recovery Current vs. Forward Current

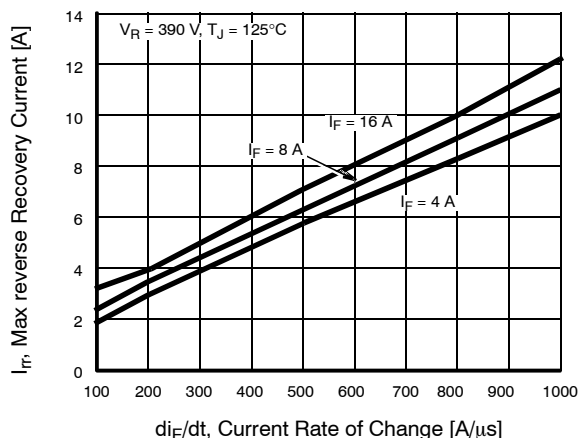


Figure 6. Maximum Reverse Recovery Current vs.  $di_F/dt$

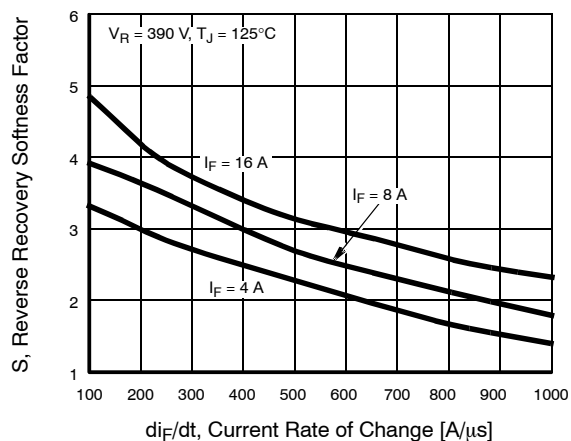


Figure 7. Reverse Recovery Softness Factor vs.  $di_F/dt$

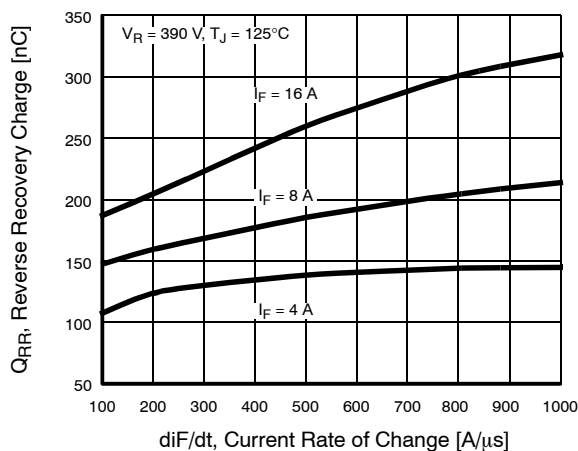


Figure 8. Reverse Recovery Charge vs.  $di_F/dt$

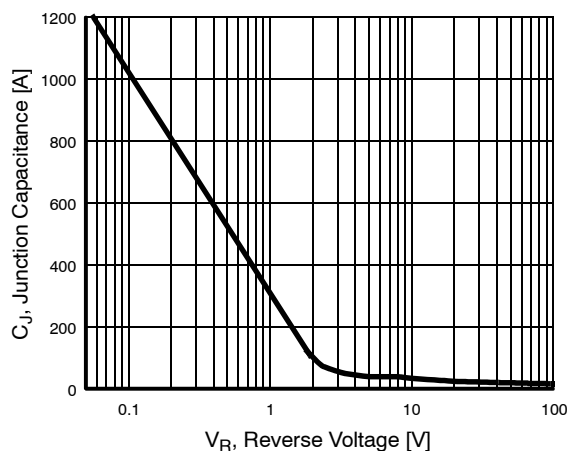


Figure 9. Junction Capacitance vs. Reverse Voltage

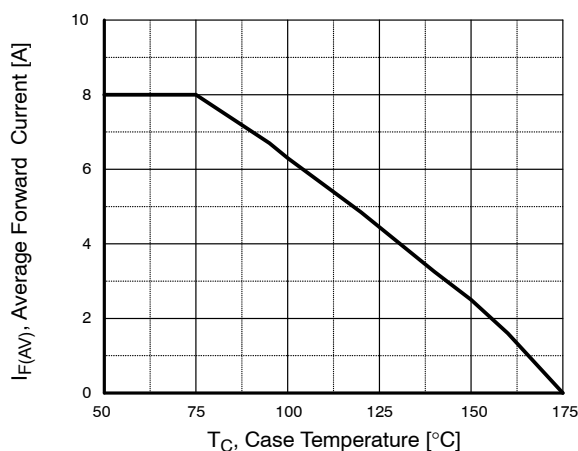


Figure 10. DC Current Derating Curve

TYPICAL CHARACTERISTICS (continued)

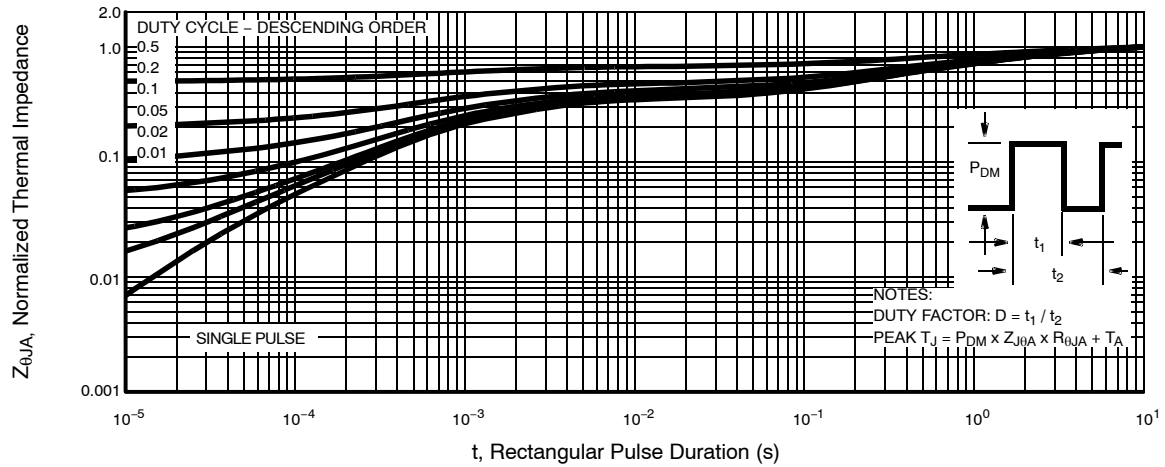


Figure 11. Normalized Maximum Transient Thermal Impedance

TEST CIRCUIT AND WAVEFORMS

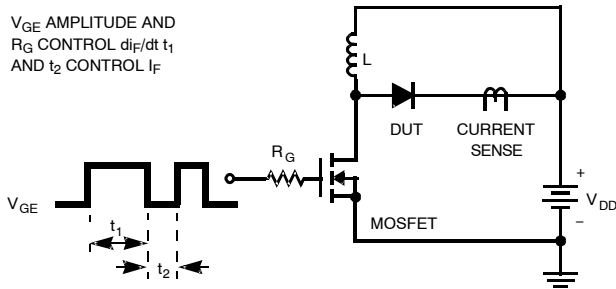


Figure 12.  $t_{rr}$  Test Circuit

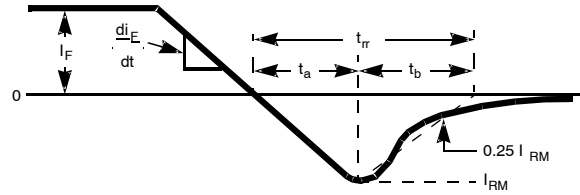


Figure 13.  $t_{rr}$  Waveforms and Definitions

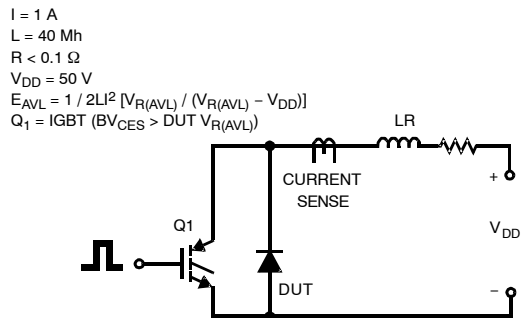


Figure 14. Avalanche Energy Test Circuit

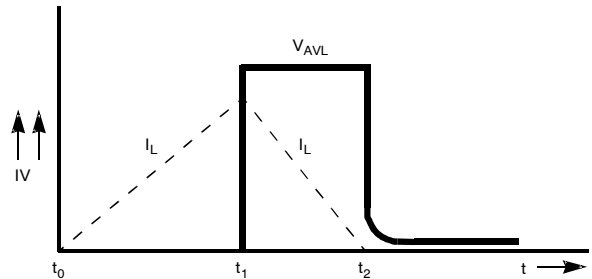
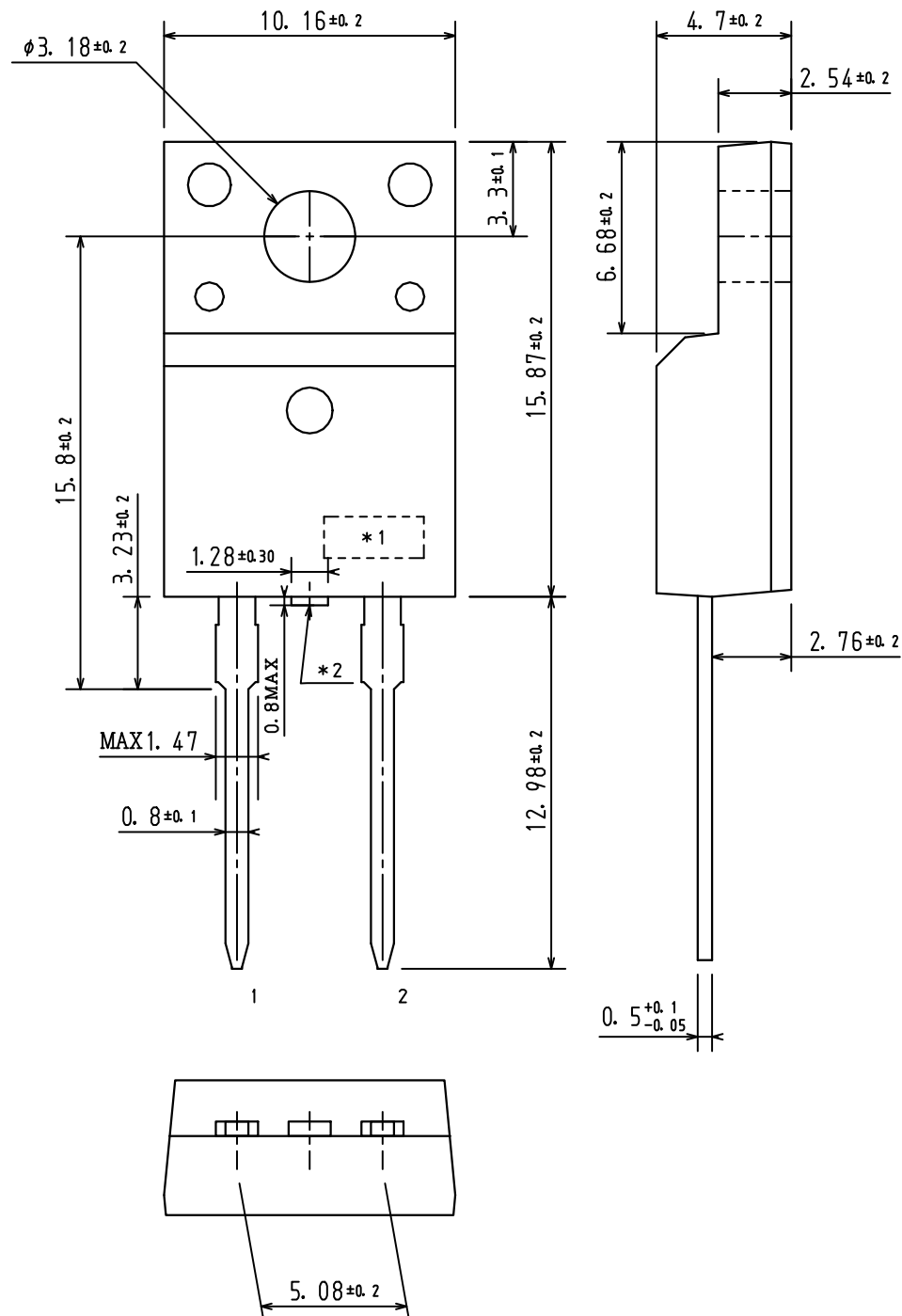


Figure 15. Avalanche Current and Voltage Waveforms

**TO-220 Fullpack, 2-Lead / TO-220F-2FS**  
CASE 221AS  
ISSUE O

DATE 29 FEB 2012



|                         |                                              |                                                                                                                                                                                     |
|-------------------------|----------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
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